Mega Power Dual IGBT Modules

(with 6th Gen. IGBT Chips)

Application

High Power Energy Conversion

Features

- 6th Generation IGBT with CSTBT™ Chip Technology
- For 1200V modules: $V_{CE(sat)}$ = 1.7V(typ) @ T_j = 125°C; wide SOA @ V_{cc} = 900V
- For 1700V modules: $V_{CE(sat)}$ = 2.2V(typ) @ T_j = 125°C; wide SOA @ V_{cc} = 1200V
- $T_{j(max)}$ = 175°C
- New solderless Al-baseplate → high ΔT_c temperature cycling capability
- Wide internal chip layout → low $R_{th(j-f)}$
- Minimized internal package inductance L_{int} = 5.1nH (large package)
- AC and DC main terminals separated → easy DC-bus design
- Multi-hole main terminals → low contact resistance and reliable long-term electrical connection
- Integrated NTC for T_c-sensing
- Auxiliary C-terminals available for P- and N-side IGBT

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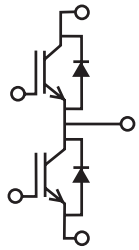
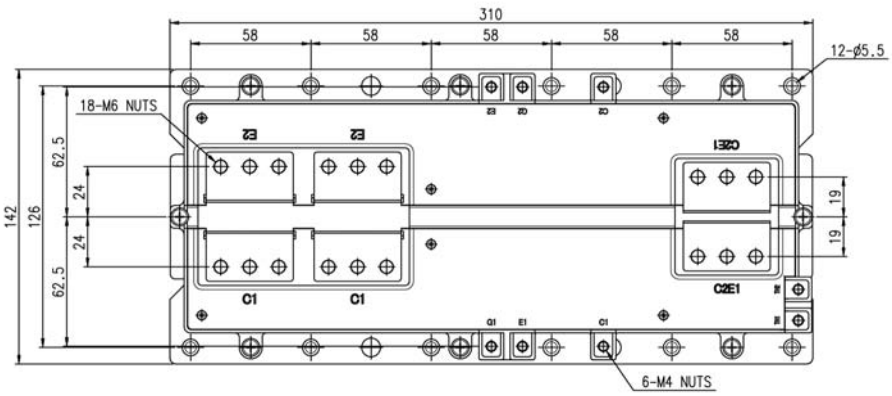
Line-up

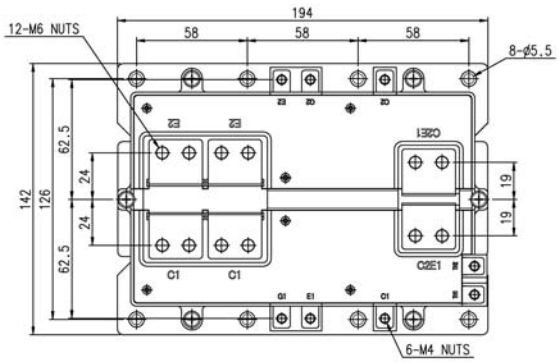
Package		Size	A		B	
Symbol	Circuit Diagram	V_{CES} (V)	I_C (A)			
			1100	1500	1800	2500
D		1200		CM1500DY-24S		CM2500DY-24S
		1700	CM1100DY-34S		CM1800DY-34S	

under development

Large Package Type (L 310 x W 142 x H 50mm)



Small Package Type (L 194 x W 142 x H 50mm)



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